

ABSTRACT

In a semiconductor device comprising a fuse 11 which makes connection between a first interconnection 10 and a second interconnection 12, and a first low heat-conductive section 13 which makes connection between the first interconnection 10 and a third interconnection 14 at a site of the first interconnection 10 where the fuse 11 is not connected, the first low heat-conductive section 13 is fabricated from a material having a heat conductivity lower than that of the material to form the first interconnection 10. When the fuse is blown with the laser beam irradiation, the heat dissipation through the heat conduction along the fuse and the interconnection is to be suppressed, and thereby a satisfactory disconnection at the fuse is to be achieved.